Silicon FS Trench IGBT

电气特性/ Features And Benefits:

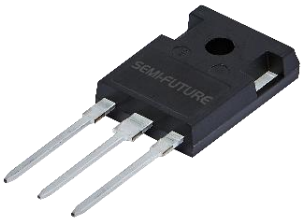
- 650V 沟槽栅/场终止工艺

  650V trench gate/field termination process
- 低开关损耗

  Low switching losses
- Vcesat 正温度系数

  Vcesat has a positive temperature coefficient

典型应用/Applications:



- 充电桩

  Charging station
- OBC

  On board charger
- 不间断电源

  Uninterruptible power supplies
- 逆变器

  Inverters

关键性能和程序参数 / Key Performance And Package Parameters

Type	V_{CE}	I_C	VCEsat, T_{vj}=25°C	T_{vjmax}	Package
SD50N07A6	650V	50A	1.58V	175°C	TO-247-3L

双极晶体管/IGBT

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
集电极-发射极电压 Collector-EmitterVoltage	T_{vj}=25°C	V_{CES}	650	V
连续集电极直流电流 Continuous DC collector current	T_C=25°C, $T_{vj\ max}$=175°C T_C=100°C, $T_{vj\ max}$=175°C	I_C	80 50	A

集电极脉冲电流 Pulsed collector current, tp limited by $T_{vj\ max}$		I_{Cpuls}	200	A
总功率损耗 Total power dissipation	T_C =25°C, $T_{vj\ max}$ =175°C T_C =100°C, $T_{vj\ max}$ =175°C	P_{tot}	295 150	W
栅极-发射极电压 Gate emitterVoltage	t_p ≤10μs, D<0.010	V_{GE}	±20 30	V
在开关状态下温度 Temperature under switching conditions		$T_{vj\ op}$	-40…+175	℃
储存温度 Storage temperature		T_{stg}	-40…+150	℃

热特性 / Thermal Characteristics

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
热阻，结-环境 Thermal resistance, junction-ambient		$R_{th(j-a)}$			40	K/W
IGBT 热阻，结-壳 IGBT thermal resistance, junction - case		$R_{th(j-C)}$		0.51		K/W

特征值 / Characteristic Values

Parameter	Conditions		Symbol	Value			Unit
				Min.	Typ.	Max.	
击穿电压 Collector-emitter breakdown voltage	VGE=0V, IC=0.25mA		$V_{(BR)CES}$	650			V
集电极-发射极饱和电压 Collector-Emitter saturationVoltage	V_{GE}=15V, I_C=50A V_{GE}=15V, I_C=50A V_{GE}=15V, I_C=50A	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	V_{CEsat}		1.58 1.87 1.95	2.10	
栅极-发射极阈值电压 Gate-Emitter thresholdVoltage	I_C=0.5mA,V_{GE}=V_{CE}	T_{vj}=25°C	$V_{GE(th)}$	4.2	5.0	5.8	
跨导 Transconductance	V_{CE}=20V，I_C=50A		G_{fs}		77		S
输入电容 Input capacitance	f=100kHz,V_{CE}=25V,V_{GE}=0V	T_{vj}=25°C	C_{ies}		5.46		nF
输出电容 Output capacitance			C_{oes}		0.20		
反向传输电容 Reverse transfer capacitance			C_{res}		0.10		
门极电荷 Gate charge	I_C =50A,V_{GE} =15V, V_{CE} =520V	T_{vj}=25°C	Q_G		0.53		μC
集电极-发射极截止电流 Collector-emitter cut-off current	V_{CE}=650V ,V_{GE}=0V	T_{vj}=25°C T_{vj}=175°C	I_{CES}		2000	50	uA
栅极-发射极漏电流 Gate-emitter leakage current	V_{CE}=0V,V_{GE}=20V	T_{vj}=25°C	I_{GES}			100	nA

开通延迟时间 Turn-on delay time	I_C=50A,V_{CE}=400V V_{GE}=±15V, R_G=8Ω (电感负载) / (inductive load)	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	$t_{d\ on}$		33 21 19		ns
上升时间 Rise time	I_C=50A,V_{CE}=400V V_{GE}=±15V, R_G=8Ω (电感负载) / (inductive load)	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	t_r		75 67 65		
关断延迟时间 Turn-off delay time	I_C=50A,V_{CE}=400V V_{GE}=±15V, R_G=8Ω (电感负载) / (inductive load)	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	$t_{d\ off}$		21 32 38		
下降时间 Fall time	I_C=50A,V_{CE}=400V V_{GE}=±15V, R_G=8Ω (电感负载) / (inductive load)	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	t_f		41 62 62		
开通损耗能量（每脉冲） Turn-on energy loss per pulse	I_C=50A,V_{CE}=400V V_{GE}=±15V, R_G=8Ω (电感负载) / (inductive load)	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	E_{on}		2.37 2.88 3.10		mJ
关断损耗能量（每脉冲） Turn-off energy loss per pulse	I_C=50A,V_{CE}=400V V_{GE}=±15V, R_G=8Ω (电感负载) / (inductive load)	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	E_{off}		0.60 0.73 0.76		
开关损耗能量（每脉冲） Total switching energy	I_C=50A,V_{CE}=400V V_{GE}=±15V, R_G=8Ω (电感负载) / (inductive load)	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	E_{ts}		2.97 3.61 3.86		

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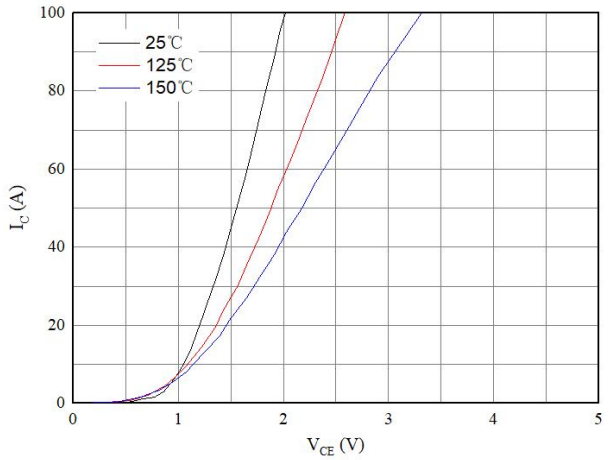


图 1. 典型输出特性 (V_{GE}=15V)

Figure 1. Typical output characteristics (V_{GE}=15V)

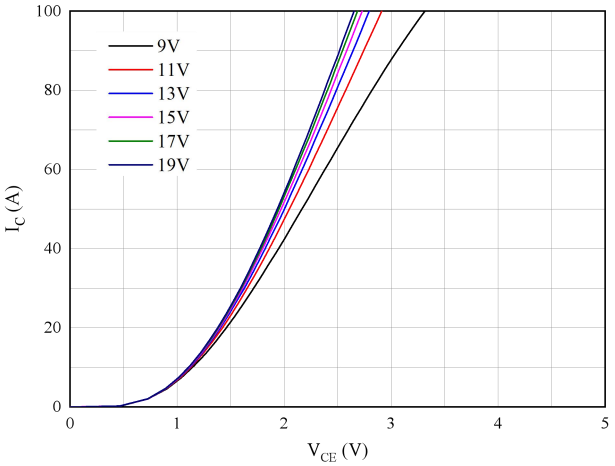


图 2. 典型输出特性 (T_{vj}=150℃)

Figure 2. Typical output characteristics (T_{vj}=150℃)

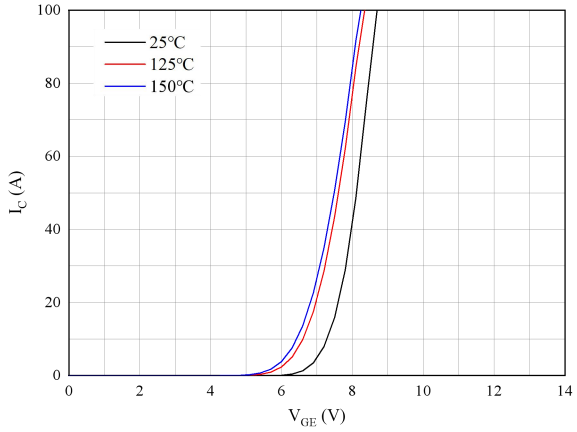


图 3. 典型传输特性(V_{CE}=20V)

Figure 3. Typical transfer characteristic(V_{CE}=20V)

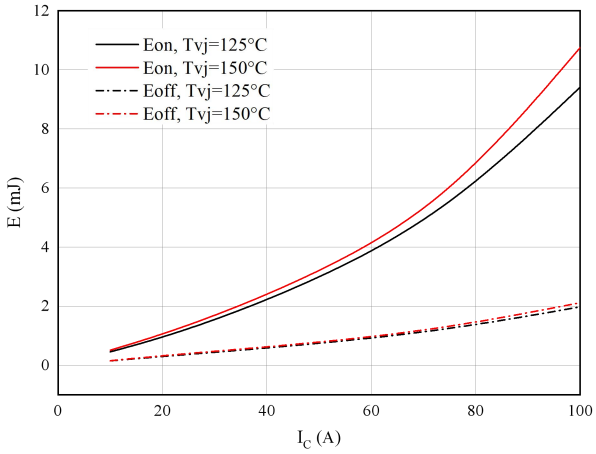


图 4. 开关损耗

Figure 4. Switching losses of IGBT

VGE=±15V, RGon=8Ω, Rgoff=8Ω,VCE=400V

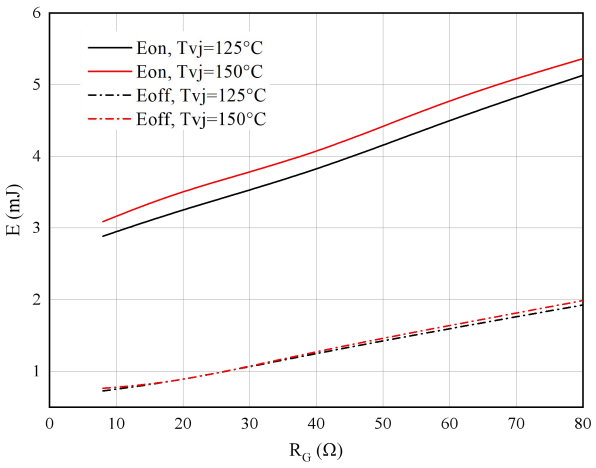


图 5. 开关损耗

Figure 5. Switching losses of IGBT

VGE=±15V, IC=50A,VCE=400V

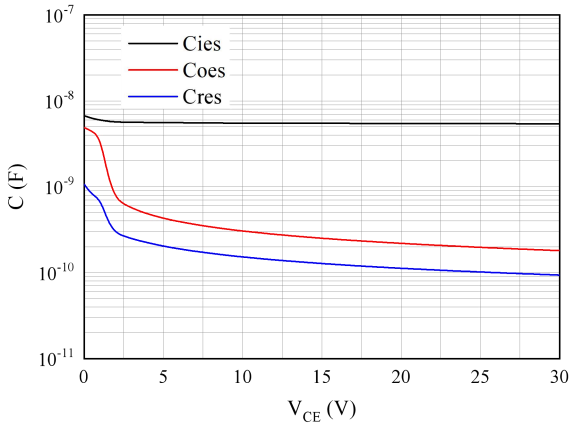


图 6 电容特性

Figure 6. Capacitance characteristic

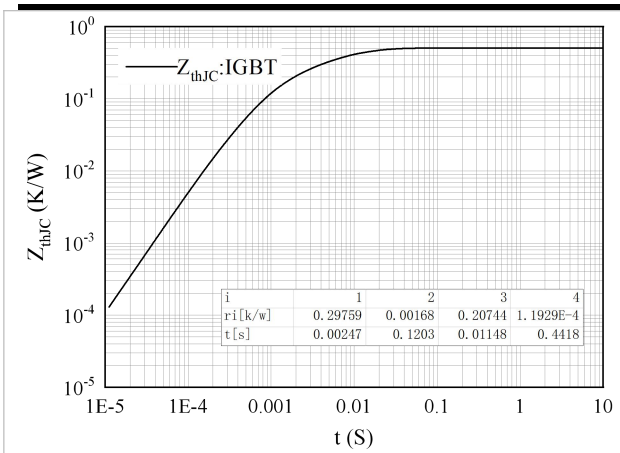
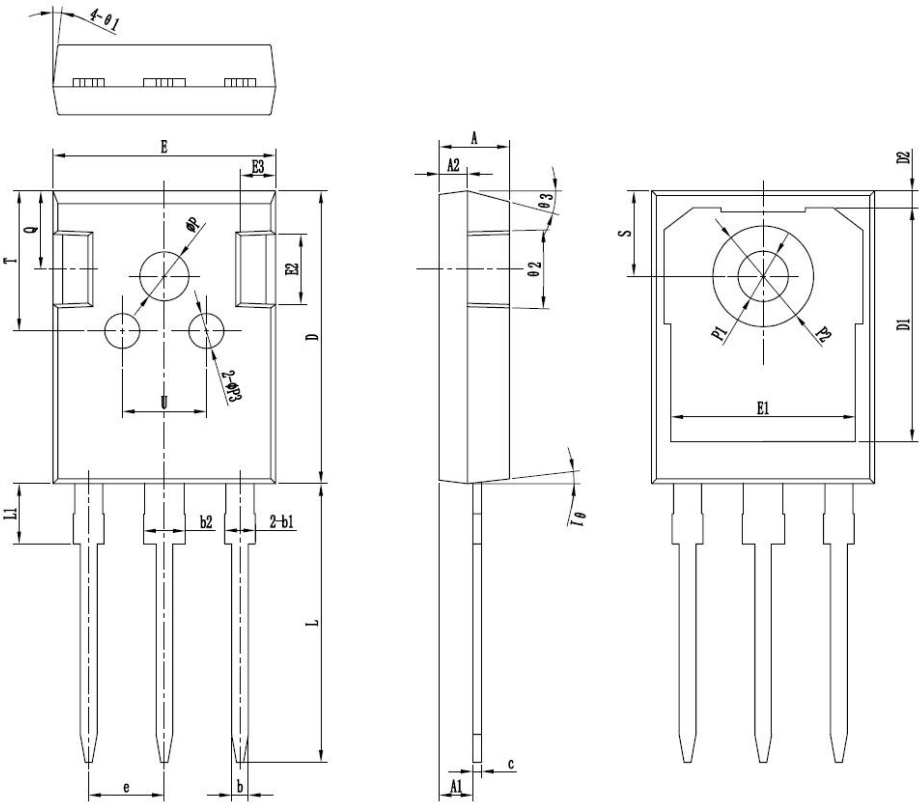


图 7. 瞬态热阻抗 IGBT

Figure 7. Transient thermal impedance IGBT, $Z_{thJC}=f(t)$

接线图 / Circuit diagram

封装尺寸 / Package outlines



符号	单位:mm		
	MIN	NOM	MAX
*A	4.90	5.00	5.10
*A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
*b	1.15	1.20	1.25
*b1	1.95	2.10	2.25
*b2	2.95	3.10	3.25
*c	0.55	0.60	0.65
*D	20.90	21.00	21.10
D1	16.35	16.55	16.75
D2	1.05	1.20	1.35
*E	15.70	15.80	15.90
E1	13.10	13.25	13.40
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
*e	5.40	5.44	5.48
*L	19.80	19.92	20.10
*L1	-	-	4.30
*ΦP	3.70	3.80	3.90
*ΦP1	3.50	3.60	3.70
ΦP2	7.00	7.20	7.40
ΦP3	2.40	2.50	2.60
Q	5.60	5.80	6.00
*S	6.05	6.15	6.25
T	9.80	10.00	10.20
U	6.00	6.20	6.40
θ1	5°	7°	9°
θ2	1°	3°	5°
θ3	13°	15°	17°

*为关键管控尺寸

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